

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	168	(silicon adj oxide) near10 (etch adj stop adj layer)	USPAT	2002/07/29 15:29
2	BRS	L2	4	(silicon adj oxide) near10 (organosilicate)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD_B	2002/07/29 15:31
3	BRS	L4	1	(organosilicate) same (etch adj stop adj layer) same (silicon adj oxide)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TD_B	2002/07/29 15:34
4	BRS	L5	35913	silicon adj oxide	USPAT	2002/07/29 15:34
5	BRS	L6	129	5 near5 (etch adj stop adj layer)	USPAT	2002/07/29 15:43
6	BRS	L7	6932	(etch or etching) near10 (silicon adj oxide)	USPAT	2002/07/29 15:43
7	BRS	L8	2	7 same (organosilicate)	USPAT	2002/07/29 16:43
8	BRS	L9	2	(organosilicate) near10 (etch or etching or etched)	USPAT	2002/07/29 16:46
9	BRS	L10	11	organosilicate near10 temperature	USPAT	2002/07/29 16:50
10	BRS	L11	175	(silicon adj oxide) near10 (etch or etched or etching) near10 pressure	USPAT	2002/07/29 16:51
11	BRS	L12	31	11 same temperature	USPAT	2002/07/29 16:51